

RF Nano Awarded National Science Foundation SBIR Phase IB Enhancing CMOS with RF Nanotube FETs

NEWPORT BEACH, June 8, 2007 –

RF Nano Corporation™, the leader in developing carbon nanotubes for analog electronics, was awarded a Phase IB proposal with the National Science Foundation Small Business Innovation Research (SBIR) Program to investigate Enhancing CMOS with Nanotube FETs. The Phase IB project will expand upon the successful completion of our Phase IA efforts and focus on developing full commercial prototypes of Carbon Nanotube Field Effect Transistors (CNT FETs) using standard CMOS processes. The effort will culminate in delivery of sample parts for integration into prototype boards and systems.

About RF Nano

RF Nano Corporation™ is the leader in developing a CMOS compatible suite of discrete, wafer and integrated circuit products based on the outstanding analog electronic properties of carbon nanotubes. With power densities 100 times silicon and 20 times greater than gallium arsenide, intrinsic cutoff frequencies in the Terahertz, inexpensive growth, and the ability to integrate with standard CMOS processes, RF Nano's extremely robust carbon nanotubes devices will revolutionize the \$60 billion analog and mixed signal semiconductor markets. Founded in 2005 and based in Orange County, CA, the company is privately held and backed by Okapi Venture Capital. For more information, please visit www.RFNano.com.

Media Contact:

Steffen McKernan

949-955-1441

Steffen.McKernan@RFNano.com